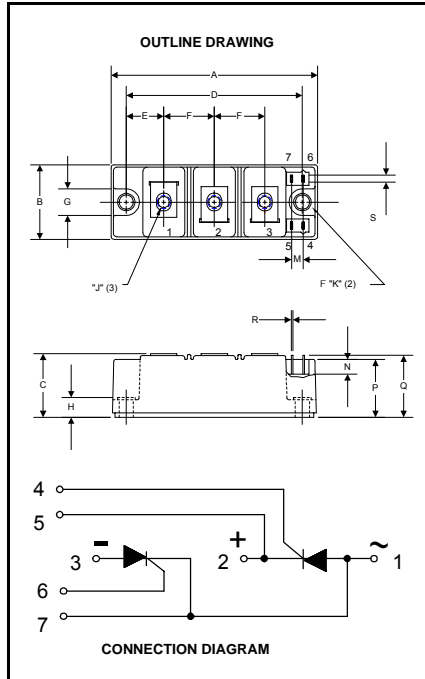


**POW-R-BLOK™**  
**Dual SCR Isolated Module**  
**150 Amperes / Up to 1600 Volts**



**CD63\_\_15A**  
**Dual SCR Isolated**  
**POW-R-BLOK™ Module**  
 150 Amperes / Up to 1600 Volts

**Description:**

Powerex Dual SCR Modules are designed for use in applications requiring phase control and isolated packaging. The modules are isolated for easy mounting with other components on a common heatsink. POW-R-BLOK™ has been tested and recognized by the Underwriters Laboratories.

**Features:**

- Electrically Isolated Heatsinking
- DBC Alumina (Al<sub>2</sub>O<sub>3</sub>) Insulator
- Glass Passivated Chips
- Metal Baseplate
- Low Thermal Impedance for Improved Current Capability
- Quick Connect Gate Terminal with Provision for Keyed Mating Plug
- UL Recognized (E78240)

**CD63\_15A Outline Dimensions**

| Dimension | Inches | Millimeters |
|-----------|--------|-------------|
| A         | 3.70   | 94          |
| B         | 1.38   | 35          |
| C         | 1.18   | 30          |
| D         | 3.15   | 80          |
| E         | 0.67   | 17          |
| F         | 0.91   | 23          |
| G         | 0.57   | 14.5        |
| H         | 0.35   | 9           |
| J         | M6     | M6          |
| K         | 0.26   | 6.5         |
| M         | .020   | 5           |
| N         | 0.28   | 7           |
| P         | 1.10   | 28          |
| Q         | 1.14   | 29          |
| R         | 0.03   | 0.8         |
| S         | 0.11   | 2.8         |

Note: Dimensions are for reference only.

**Ordering Information:**

Select the complete nine digit module part number from the table below.  
 Example: CD631615A is a 1600Volt, 150 Ampere Dual SCR Isolated POW-R-BLOK™ Module

| Type | Voltage Volts (x100) | Current Amperes (x 10) |
|------|----------------------|------------------------|
| CD63 | 08                   | 15                     |
|      | 12                   |                        |
|      | 14                   |                        |
|      | 16                   |                        |

**Benefits:**

- No Additional Insulation Components Required
- Easy Installation
- No Clamping Components Required
- Reduce Engineering Time

**Applications:**

- Bridge Circuits
- AC & DC Motor Drives
- Battery Supplies
- Power Supplies
- Large IGBT Circuit Front Ends
- Lighting Control
- Heat & Temperature Control
- Welders

**Absolute Maximum Ratings**

| Characteristics   | Conditions   | Symbol                | Units                          |
|---|--|-----------------------|--------------------------------|
| Repetitive Peak Forward and Reverse Blocking Voltage      |  | $V_{DRM}$ & $V_{RRM}$ | up to 1600 V                   |
| Non-Repetitive Peak Reverse Blocking Voltage (t < 5 msec) |  | $V_{RSM}$             | $V_{RRM} + 100$ V              |
| RMS Forward Current                                       | 180° Conduction, $T_C=85^\circ\text{C}$  | $I_{T(RMS)}$          | 250 A                          |
|   | 180° Conduction, $T_C=85^\circ\text{C}$ (AC Switch)  | $I_{T(RMS)}$          | 355 A                          |
| Average Forward Current                                   | 180° Conduction, $T_C=85^\circ\text{C}$  | $I_{T(AV)}$           | 160 A                          |
|   | 180° Conduction, $T_C=90^\circ\text{C}$  | $I_{T(AV)}$           | 150 A                          |
| Peak One Cycle Surge Current, Non-Repetitive              | 60 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 4300 A                         |
|   | 60 Hz, No $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 5100 A                         |
|   | 50 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 4100 A                         |
|   | 50 Hz, No $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 4870 A                         |
| Peak Three Cycle Surge Current, Non-Repetitive            | 60 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 3250 A                         |
|   | 50 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 3150 A                         |
| Peak Ten Cycle Surge Current, Non-Repetitive              | 60 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 2650 A                         |
|   | 50 Hz, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I_{TSM}$             | 2550 A                         |
| $I^2t$ for Fusing for One Cycle                           | 8.3 ms, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$  | $I^2t$                | 76,700 $\text{A}^2\text{sec}$  |
|   | 8.3 ms, No $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$  | $I^2t$                | 108,000 $\text{A}^2\text{sec}$ |
|   | 10 ms, 100% $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I^2t$                | 84,000 $\text{A}^2\text{sec}$  |
|   | 10 ms, No $V_{RRM}$ reapplied, $T_j=125^\circ\text{C}$   | $I^2t$                | 119,000 $\text{A}^2\text{sec}$ |
| Maximum Rate-of-Rise of On-State Current, Non Repetitive  | $T_j=125^\circ\text{C}$ ,<br>$V_D = V_{DRM}$ (Rated), $I_{TM}=400\text{A}$ ,<br>$I_G=0.5\text{A}$ , $T_r < 0.25\mu\text{s}$ , $t_p > 6\mu\text{s}$ | di/dt                 | 300 $\text{A}/\mu\text{s}$     |
| Peak Gate Power Dissipation                               | $T_p < 5\text{ms}$ , $T_j = 125^\circ\text{C}$   | $P_{GM}$              | 12 W                           |
| Average Gate Power Dissipation                            | $F = 50\text{Hz}$ , $T_j = 125^\circ\text{C}$  | $P_{G(AV)}$           | 3 W                            |
| Peak Forward Gate Current                                 | $T_p < 5\text{ms}$ , $T_j = 125^\circ\text{C}$   | $I_{GFM}$             | 3 A                            |
| Peak Reverse Gate Voltage                                 | $T_p < 5\text{ms}$ , $T_j = 125^\circ\text{C}$   | $V_{GRM}$             | 10 V                           |
| Operating Temperature                                     |  | $T_J$                 | -40 to +125 $^\circ\text{C}$   |
| Storage Temperature                                       |  | $T_{stg}$             | -40 to +150 $^\circ\text{C}$   |
| Max. Mounting Torque, M6 Mounting Screw on Terminals      |  |                       | 35 - 50 in.-Lb.                |
|   |  |                       | 4 - 6 Nm                       |
| Max. Mounting Torque, Module to Heatsink                  |  |                       | 35 - 50 in.-Lb.                |
|   |  |                       | 4 - 6 Nm                       |
| Module Weight, Typical                                    |  |                       | 200 g                          |
|   |  |                       | 7.1 oz.                        |
| V Isolation @ 25C   |  | $V_{rms}$             | 3500 V                         |

**Electrical Characteristics, T<sub>J</sub>=25°C unless otherwise specified**

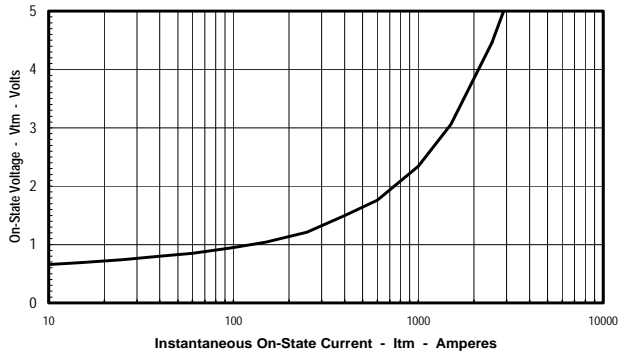
| Characteristics                          | Symbol             | Test Conditions  | Min.                     | Max.                                      | Units                   |
|--|--------------------|--|--------------------------|---|-------------------------|
| Repetitive Peak Forward Leakage Current  | I <sub>DRM</sub>   | Up to 1600V, T <sub>J</sub> =125°C   |                          | 50  | mA                      |
| Repetitive Peak Reverse Leakage Current  | I <sub>RRM</sub>   | Up to 1600V, T <sub>J</sub> =125°C   |                          | 50  | mA                      |
| Peak On-State Voltage                    | V <sub>TM</sub>    | I <sub>TM</sub> =500A  |                          | 1.54                                      | V                       |
| Threshold Voltage, Low-level             | V <sub>(TO)1</sub> | T <sub>J</sub> = 125°C, I = 16.7% x I <sub>T(AV)</sub> to I <sub>T(AV)</sub>   |                          | 0.80                                      | V                       |
| Slope Resistance, Low-level              | r <sub>T1</sub>    |  |                          | 1.67                                      | mΩ                      |
| Threshold Voltage, High-level            | V <sub>(TO)2</sub> | T <sub>J</sub> = 125°C, I = I <sub>T(AV)</sub> to I <sub>TSM</sub>   |                          | 0.98                                      | V                       |
| Slope Resistance, High-level             | r <sub>T2</sub>    |  |                          | 1.38                                      | mΩ                      |
| V <sub>TM</sub> Coefficients, Full Range |                    | T <sub>J</sub> = 125°C, I = 15% x I <sub>T(AV)</sub> to I <sub>TSM</sub><br>V <sub>TM</sub> = A + B Ln I + C I + D Sqrt I  | A =<br>B =<br>C =<br>D = | 0.5926<br>-1.10E-03<br>1.03E-03<br>0.0241 |                         |
| Minimum dV/dt                            | dV/dt              | Exponential to 2/3 V <sub>DRM</sub><br>T <sub>J</sub> =125°C, Gate Open  | 1000                     |   | V/μs                    |
| Turn-On Time (Typical)                   | t <sub>on</sub>    | I <sub>TM</sub> = 300A, V <sub>D</sub> = 2/3 V <sub>DRM</sub> dI/dt = 1A/μs  | 3                        | (Typical)                                 | μs                      |
| Turn-Off Time (Typical)                  | t <sub>off</sub>   | T <sub>J</sub> = 125°C, I <sub>T</sub> = 300A, R <sub>gk</sub> = 100Ω<br>V <sub>r</sub> = 50V, -dI/dt = 15 A/μs<br>Re-Applied dV/dt = 20V/μs,<br>Linear to 2/3 V <sub>DRM</sub>  | 50 - 200                 | (Typical)                                 | μs                      |
| Gate Trigger Current                     | I <sub>GT</sub>    | T <sub>J</sub> = -40°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load<br>T <sub>J</sub> = 25°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load<br>T <sub>J</sub> =125°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load |                          | 270<br>150<br>80                          | mA<br>mA<br>mA          |
| Gate Trigger Voltage                     | V <sub>GT</sub>    | T <sub>J</sub> = -40°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load<br>T <sub>J</sub> = 25°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load<br>T <sub>J</sub> =125°C, V <sub>D</sub> =6V, R <sub>a</sub> =1Ω, Resistive Load |                          | 4.0<br>2.5<br>1.7                         | Volts<br>Volts<br>Volts |
| Non-Triggering Gate Voltage              | V <sub>GDM</sub>   | T <sub>J</sub> =125°C, V <sub>D</sub> =V <sub>DRM</sub>  |                          | 0.30                                      | Volts                   |
| Non-Triggering Gate Current              | I <sub>GDM</sub>   | T <sub>J</sub> =125°C, V <sub>D</sub> =V <sub>DRM</sub>  |                          | 10  | mA                      |

**Thermal Characteristics**

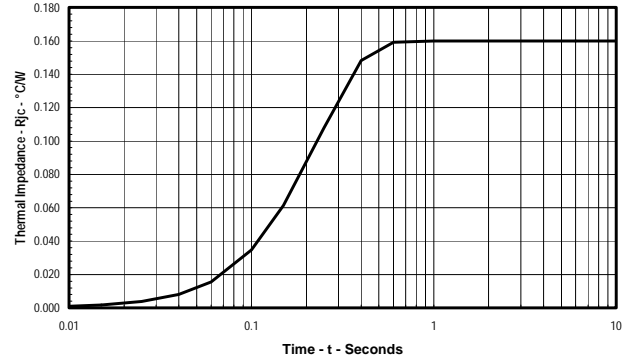
| Characteristics                                      | Symbol            |  | Max.   | Units   |
|--|-------------------|--|--|---|
| Thermal Resistance, Junction to Case<br>DC Operation | R <sub>ΘJ-C</sub> | Per Module, both conducting<br>Per Junction, both conducting   | 0.08<br>0.16   | °C/W<br>°C/W  |
| Thermal Impedance Coefficients<br>(Per Junction)     | Z <sub>ΘJ-C</sub> | Z <sub>ΘJ-C</sub> = K <sub>1</sub> (1-exp(-t/τ <sub>1</sub> ))<br>+ K <sub>2</sub> (1-exp(-t/τ <sub>2</sub> ))<br>+ K <sub>3</sub> (1-exp(-t/τ <sub>3</sub> ))<br>+ K <sub>4</sub> (1-exp(-t/τ <sub>4</sub> )) | K <sub>1</sub> = 5.45334E-3<br>K <sub>2</sub> = 3.8509E+1<br>K <sub>3</sub> = -3.5154E+1<br>K <sub>4</sub> = -3.20 | τ <sub>1</sub> = 4.511E-5<br>τ <sub>2</sub> = 1.3558E-1<br>τ <sub>3</sub> = 1.3311E-1<br>τ <sub>4</sub> = 1.5936E-1 |
| Thermal Resistance, Case to Sink Lubricated          | R <sub>ΘC-S</sub> | Per Module   | 0.05   | °C/W  |

### POW-R-BLOK™ Dual SCR Isolated Module 150 Amperes / Up to 1600 Volts

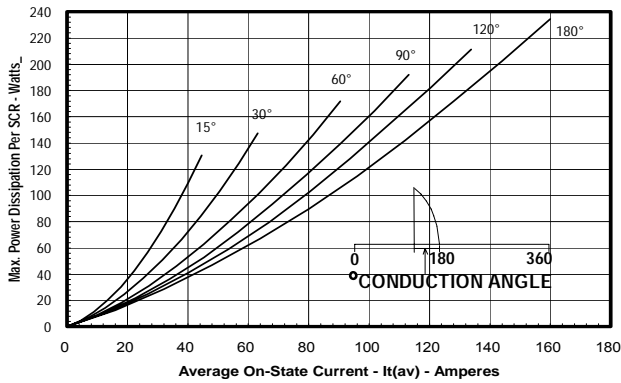
**Maximum On-State Forward Voltage Drop**  
( $T_j = 125^\circ\text{C}$ )



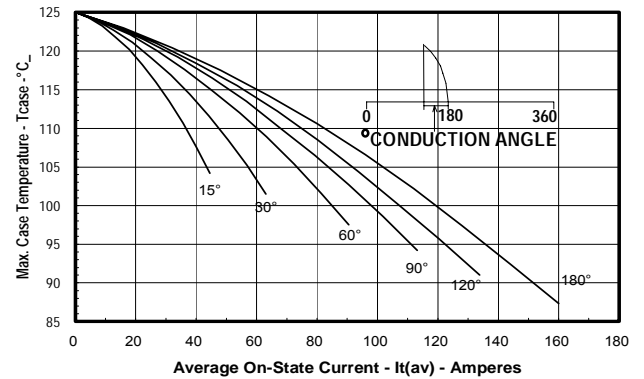
**Maximum Transient Thermal Impedance**  
(Junction to Case)



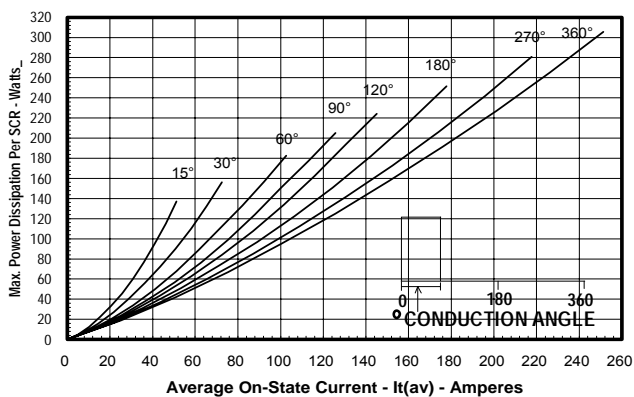
**Maximum On-State Power Dissipation**  
(Sinusoidal Waveform)



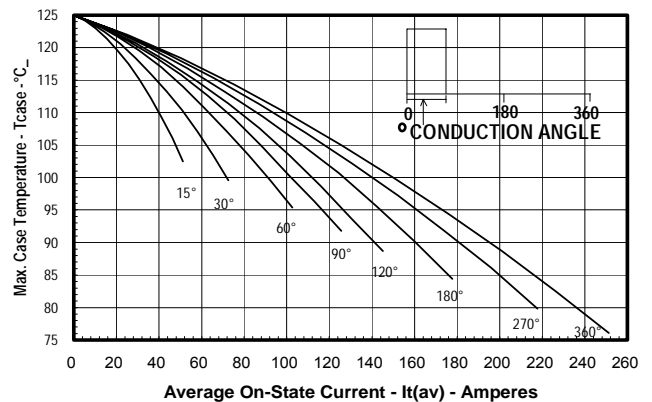
**Maximum Allowable Case Temperature**  
(Sinusoidal Waveform)

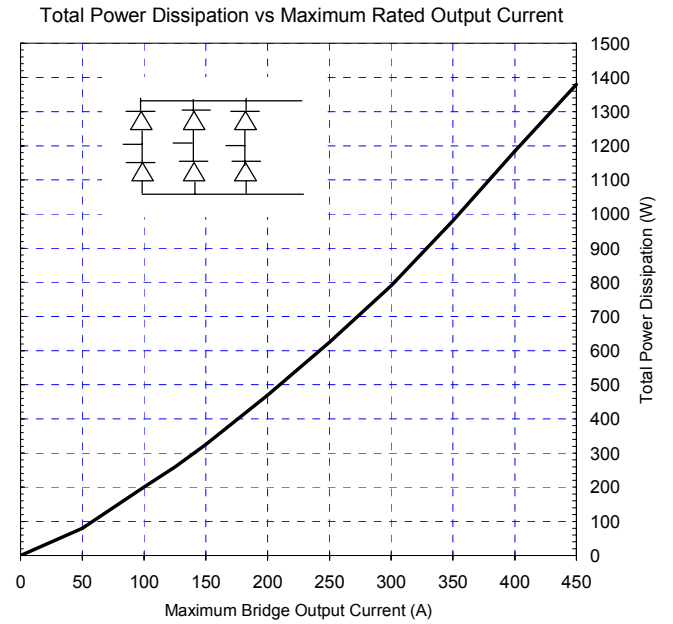
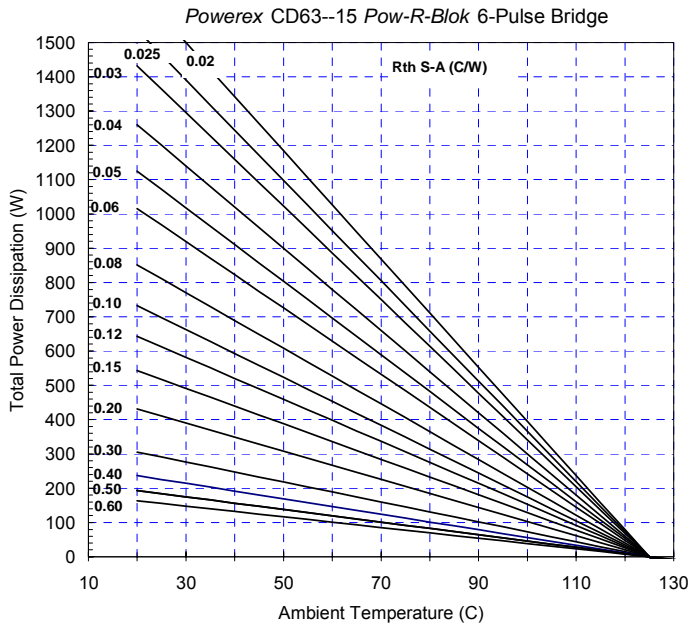


**Maximum On-State Power Dissipation**  
(Rectangular Waveform)



**Maximum Allowable Case Temperature**  
(Rectangular Waveform)





Six-Pulse Bridge Circuit Total Power Dissipation & Maximum Rated Output Current With Sink to Ambient Resistance of Heatsink as a Parameter.